

ABSTRACT OF THE DISCLOSURE

An organic switching memory device includes a plurality of first electrode lines; an organic memory layer formed on the plurality of first electrode lines, the organic memory layer
5 having a voltage-current hysteresis characteristic; a semiconductor diode layer stacked on the organic memory layer; and a plurality of second electrode lines formed on the semiconductor diode layer, the plurality of second electrode lines being disposed in a direction so as to intersect the
10 plurality of first electrode lines.